TECHNICAL DATA
DATA SHEET 4773, REV. A

HERMETIC SCHOTTKY RECTIFIER
Low Forward Voltage Drop

Features:

- **Soft Reverse Recovery at Low and High Temperature**
- **Low Forward Voltage Drop**
- **Low Power Loss, High Efficiency**
- **High Surge Capacity**
- **Guard Ring for Enhanced Durability and Long Term Reliability**
- **Guaranteed Reverse Avalanche Characteristics**

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single)	15	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave (per leg)	280	A
Non-Repetitive Avalanche Energy	E_{AS}	T_J = 25 °C, I_{AS} = 3.0 A, L = 4.4 mH (per leg)	20	mJ
Repetitive Avalanche Current	I_{AR}	I_{AS} decay linearly to 0 in 1 µs f limited by T_J max V_A=1.5V_R	3.0	A
Maximum Thermal Resistance	$R_{\theta JC}$	Per Package	1.21	°C/W
Max. Junction Temperature	T_J	-	-65 to +175	°C
Max. Storage Temperature	T_{stg}	-	-65 to +175	°C

Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)	V_{F1}	@ 15A, Pulse, T_J = 25 °C	0.97	V
	V_{F2}	@ 15A, Pulse, T_J = 125 °C	0.81	V
Max. Reverse Current (per leg)	I_{R1}	@V_R = 150V, Pulse, T_J = 25 °C	0.5	mA
	I_{R2}	@V_R = 150V, Pulse, T_J = 125 °C	8	mA
Max. Junction Capacitance (per leg)	C_T	@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz, V_{SIG} = 50mV (p-p)	500	pF

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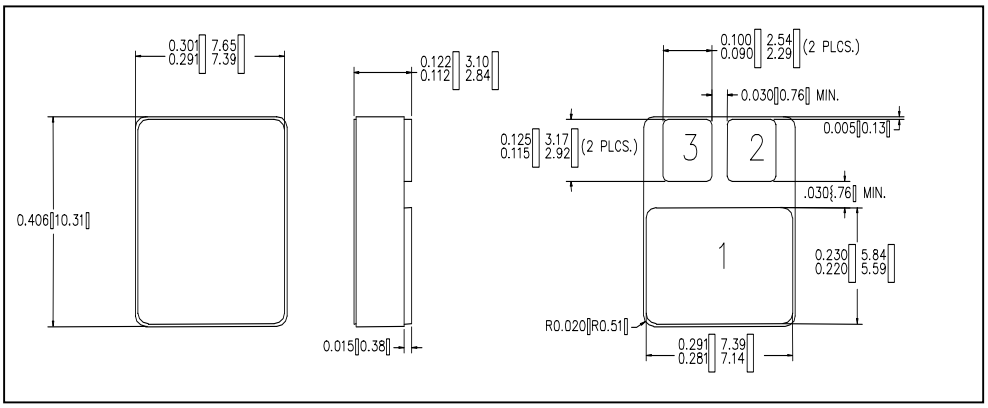
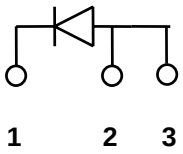
Mechanical Dimensions: in Inches / mm

LCC-5



SINGLE



PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

Note: The V_f curves shown are for the SD125SC150 unpackaged die only.

TECHNICAL DATA

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